L1: (218835) ROM or (read adj only adj memory)
L2: (11956) 1 and (MOSFET$1 or (metal adj oxide adj semiconductor) or (field ad
L3: (855) 2 and (mask$1 or photoresist$1 or resist$1).clm.
L4: (237) 3 and trench$1
L5: (155) 4 and dielectric
L6: (10) 5 and ((code$1 or coding) with (photoresist$1 or resist$1 or mask$1 or
L7: (243) 2 and (trench$1.clm.)
L8: (24) 7 and (code$1 or coding)
L9: (1739) 2 and (ROM or (read adj only adj memory)).clm.
L10: (183) 9 and (trench$1 or hole$1 or opening$1).clm.
L11: (68) 10 and (code or coded or coding)
L12: (0) 11 and (on and off)
L13: (13) 11 and (off adj state)
L14: (66) 11 and (transistor$1 or gate$1 or source$1 or drain$1)
L15: (47) 11 and (transistor$1 or gate$1 or source$1 or drain$1).clm.
L16: (0) 15 and (deep adj2 trench$2)
L17: (7) 15 and (trench$2).clm.
L18: (16778) rom.clm. or (read adj only adj memory).clm.
L19: (5087) 18 and (gate or source or drain or transistor).clm.
L20: (972) 19 and (coded or code or coding).clm.
L21: (101) 20 and (trench$2 or opening$1).clm.
L22: (72) 21 and (photoresist or resist or mask)
L23: (0) 22 and (deep adj trench$2)
L24: (67) 22 and (etch$3 or pattern$3).clm.
L25: (32) 24 and ((fill$3 or dielectric) near7 (trench$2 or opening$1))
L26: (43) 24 and ((fill$3 or deposit$3 or dielectric) near7 (trench$2 or openin
L27: (6) 26 and (turn adj around adj time)
L29: (25) 28 and ((coding or code$1) near7 (photoresist or resist or mask)).clm
L28: (37) 26 and ((coding or code$1) near7 (photoresist or resist or mask))

26 and ((coding or code$1) near7
(photoresist or resist or mask))

#	U	I	PT	P	Document ID	Issue Date	Pages	Title	Current OR	Current XR	Retrieval	Inventor	E	C			
1	☑	☐	☐	☐	US 20040077131	20040422	12	MASK ROM STRUCTURE AND MANUFACTURING METHOD TH	438/128			Chang, Ching-Yu	☐	☐	☐	☐	☐
2	☑	☐	☐	☐	US 20030211695	20031113	12	METHODS OF FABRICATING HIGH DENSITY MASK ROM C	438/276			Chang, Ching-Yu	☐	☐	☐	☐	☐
3	☑	☐	☐	☐	US 20030134478	20030717	10	Non-volatile memory and fabrication thereof	438/275	257/E21.667;		Lai, Han-Chao et al.	☐	☐	☐	☐	☐
4	☑	☐	☐	☐	US 20030132488	20030717	10	Non-volatile memory and fabrication thereof	257/390	257/391; 257/E21.66		Lai, Han-Chao et al.	☐	☐	☐	☐	☐
5	☑	☐	☐	☐	US 20030122171	20030703		VERTICAL READ-ONLY MEMORY AND FABRICATION	257/296	257/E21.671;		Huang, Shui-Chin	☐	☐	☐	☐	☐
6	☑	☐	☐	☐	US 20020168822	20021114	14	METHOD OF FABRICATING MASK READ ONLY MEMORY	438/278	257/E21.673;		Yang, Chun-Yi et al.	☐	☐	☐	☐	☐
7	☑	☐	☐	☐	US 20020094645	20020718		Process for making mask ROM using a salicide or	438/283	257/E21.672;		Shiau, Jiann-Ming	☐	☐	☐	☐	☐

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